

1. Thin film solar cell technologies such as amorphous silicon, copper indium gallium selenide, and cadmium telluride belong to which generation?

- ☐ 1<sup>st</sup> generation
- ☒ 2<sup>nd</sup> generation
- ☐ 3<sup>rd</sup> generation



**Correct**

That is correct

Thin film solar cells using direct bandgap materials are referred to as second generation solar cells.

2. Amorphous silicon has a higher bandgap (1.7 eV) than crystalline silicon (c-Si) (1.1 eV)

Which part of the spectrum is absorbed to a higher degree by the crystalline solar cell as compared to the amorphous silicon solar cell.

- ☒ Infrared
- ☐ Ultraviolet
- ☐ X-ray

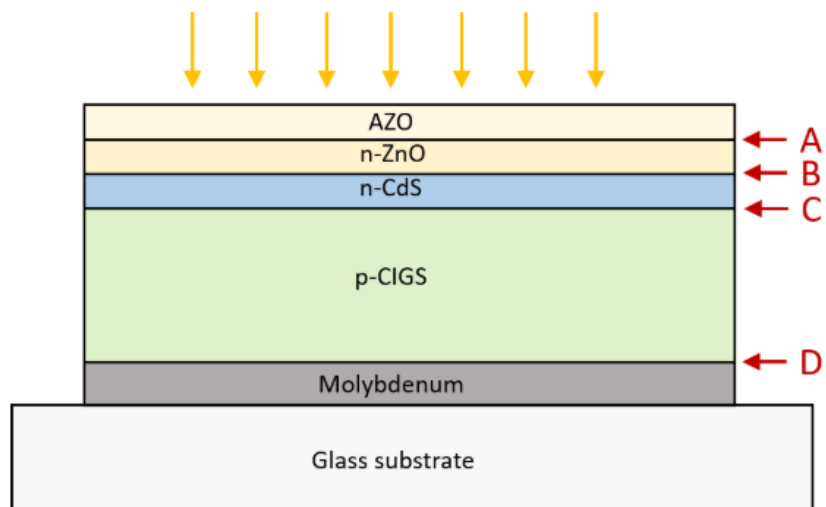


**Correct**

That is correct

A lower bandgap material absorbs light at higher wavelength as compared to a material with a higher bandgap.

3. Which interface in the CIGS solar cell is the pn-junction?



- ☐ A
- ☐ B
- ☒ C
- ☐ D



**Correct**

That is correct

The pn-junction is formed between the CIGS absorber layer and the CdS buffer layer. Unlike a silicon solar cell, the junction is a heterojunction, since it is a junction between two dissimilar semiconductors.